

# INCHANGE SEMICONDUCTOR

# **isc** Silicon NPN Power Transistors

# TIP29

## DESCRIPTION

- Collector-Emitter Sustaining Voltage-: V<sub>CEO(SUS)</sub> = 40V(Min)
- Collector-Emitter Saturation Voltage-: V<sub>CE(sat)</sub> = 0.7V(Max.)@I<sub>C</sub>= 1.0A
- Complement to Type TIP30
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

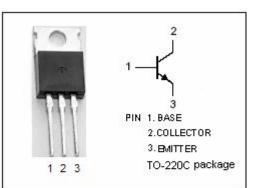
• Designed for use in general purpose amplifier and switching applications.

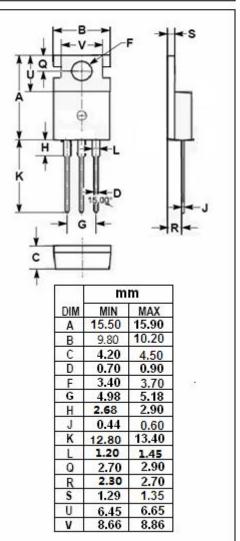
SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	40	V
Vceo	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
lc	Collector Current-Continuous	1	А
I <sub>CM</sub>	Collector Current-Pulse	3	А
I <sub>B</sub>	Base Current 0.4		А
Pc	Collector Power Dissipation $T_{C}\text{=}25^{\circ}\!^{\circ}\text{C}$	30	W
Tj	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Ttemperature Range	-65~150	°C

#### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth j-c	Thermal Resistance, Junction to Case	4.17	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	62.5	°C/W





isc Website: <u>www.iscsemi.com</u>

<sup>1</sup> *isc & iscsemi* is registered trademark



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## **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	40		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.125A		0.7	V
$V_{\text{BE}(\text{on})}$	Base-Emitter On Voltage	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V		1.3	v
Ices	Collector Cutoff Current	V <sub>CE</sub> = 40V; V <sub>EB</sub> = 0		0.2	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30V; I <sub>B</sub> = 0		0.3	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 4V	40		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	15	75	
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A ; V <sub>CE</sub> = 10V; f= 1MHz	3		MHz

## **NOTICE:**

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